Abstracts

18-40 GHz 13 dBm Low Noise GaAs FET YIG Tuned Oscillator

A.P.S. Khanna and J. Hauptman. "18-40 GHz 13 dBm Low Noise GaAs FET YIG Tuned Oscillator." 1991 MTT-S International Microwave Symposium Digest 91.1 (1991 Vol. I [MWSYM]): 209-212.

A fundamental YIG-tuned oscillator has been devel-oped using a submicron GaAs FET to cover 18 to 40 GHz. Power output of +13 dBm and phase noise of better than -100 dBc/Hz at 100 kHz from the carrier has been achieved. The approach used to design the oscillator circuit and the magnet for the oscillator will be discussed and test data will be presented.

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